

## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

	Characteristic	Symbol	Value	Unit	
Drain Source Voltage		$V_{DSS}$	50	V	
Gate-Source Voltage		$V_{GSS}$	±20	V	
Drain Current (Note 5)	Continuous	1-	300	m^	
	Pulsed (Note 6)	ID	800	mA	

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$P_{D}$	250	mW
Thermal Resistance, Junction to Ambient	R <sub>0JA</sub>	500	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +150	°C

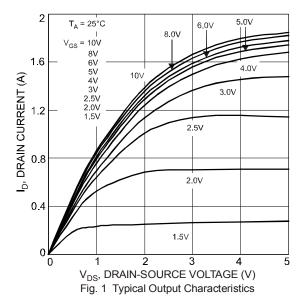
## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

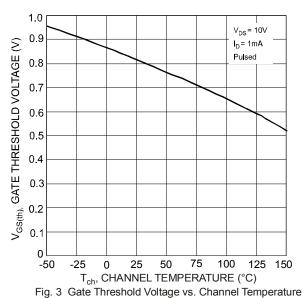
Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage		$BV_{DSS}$	50	_	_	V	$V_{GS} = 0V, I_D = 10\mu A$	
Zero Gate Voltage Drain Current	@T <sub>C</sub> = +25°C	I <sub>DSS</sub>	_	_	60	nA	$V_{DS} = 50V, V_{GS} = 0V$	
					1	μA	$V_{GS} = \pm 12V, V_{DS} = 0V$	
Gate-Body Leakage		I <sub>GSS</sub>	_	_	500	nA	$V_{GS} = \pm 10V$ , $V_{DS} = 0V$	
					50	nA	$V_{GS} = \pm 5V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage		V <sub>GS(th)</sub>	0.49	_	1.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
	On-Resistance	R <sub>DS (ON)</sub>	_	_	3.0	Ω	$V_{GS} = 1.8V, I_D = 50mA$	
Static Drain-Source On-Resistance			_	_	2.5		$V_{GS} = 2.5V, I_D = 50mA$	
			_	_	2.0		$V_{GS} = 5.0V, I_D = 50mA$	
On-State Drain Current		I <sub>D(ON)</sub>	0.5	1.4	_	Α	$V_{GS} = 10V, V_{DS} = 7.5V$	
Forward Transconductance		Y <sub>fs</sub>	200	_		mS	$V_{DS} = 10V, I_D = 0.2A$	
Source-Drain Diode Forward Voltage		$V_{SD}$	0.5	_	1.4	V	$V_{GS} = 0V, I_{S} = 115mA$	
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance		C <sub>iss</sub>	_	_	50	pF		
Output Capacitance		Coss	_	_	25	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V f = 1.0MHz	
Reverse Transfer Capacitance		Crss	_	_	5.0	pF		
Turn-On Delay Time		$t_{D(on)}$	_	2.1	_	ns		
Turn-On Rise Time		tr	_	1.8	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$ $R_{G} = 25\Omega, I_{D} = 200mA$	
Turn-Off Delay Time		$t_{D(off)}$	_	14.4		ns		
Turn-Off Fall Time		t <sub>f</sub>	_	8.4	_	ns		

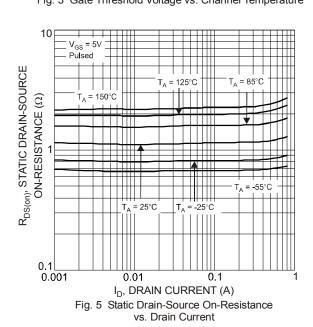
Notes:

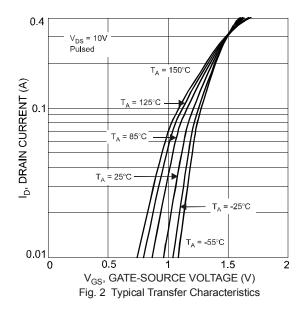
- 5. Device mounted on FR-4 PCB.
- Pulse width ≤10µS, Duty Cycle ≤1%.
  Short duration pulse test used to minimize self-heating effect.
  Guaranteed by design. Not subject to production testing.











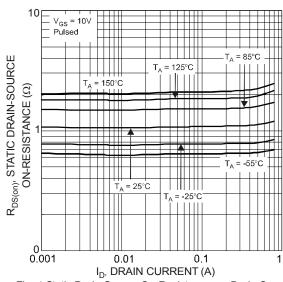
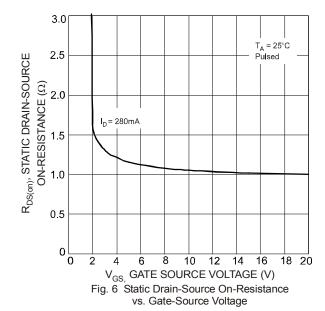


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current





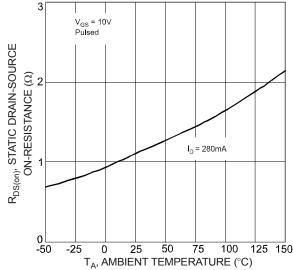


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

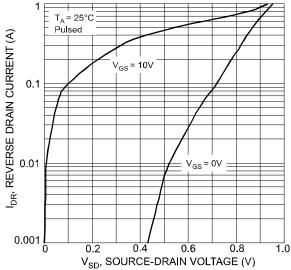
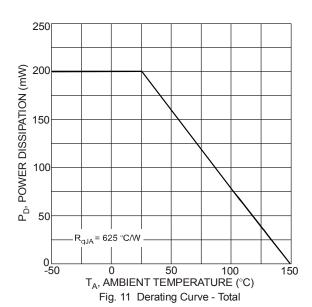


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage



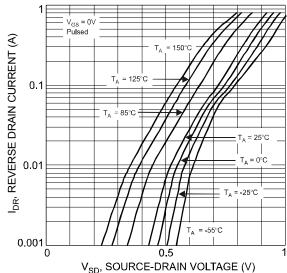


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

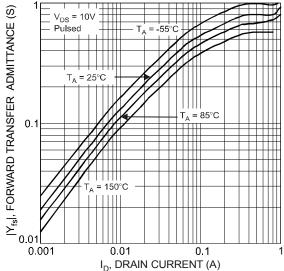
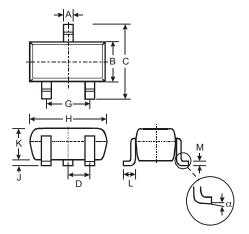


Fig. 10 Forward Transfer Admittance vs. Drain Current



### **Package Outline Dimensions**

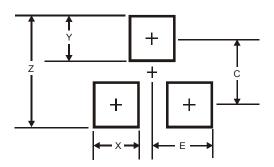
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SOT-323				
Dim	Min	Max	Тур		
Α	0.25	0.40	0.30		
В	1.15	1.35	1.30		
С	2.00	2.20	2.10		
D	1	1	0.65		
G	1.20	1.40	1.30		
Н	1.80	2.20	2.15		
J	0.0	0.10	0.05		
K	0.90	1.00	0.95		
L	0.25	0.40	0.30		
M	0.10	0.18	0.11		
α	0°	8°	-		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
Z	2.8		
X	0.7		
Y	0.9		
С	1.9		
F	1.0		



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